

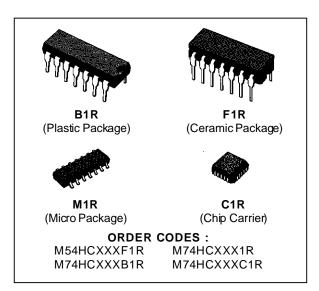
M54/74HC266 M54/74HC7266

HC266 QUAD EXCLUSIVE NOR GATE WITH OPEN DRAIN HC7266 QUAD EXCLUSIVE NOR GATE

- HIGH SPEED
 - $t_{PD} = 10 \text{ ns} (TYP.) AT V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION $I_{CC} = 1 \mu A (MAX.) AT T_A = 25 ^{\circ}C$
- HIGH NOISE IMMUNITY

 VNIH = VNIL = 28 % VCC (MIN.)
- OUTPUT DRIVE CAPABILITY
 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE (7266) |I_{OH}| = I_{OL} = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS (7266)

 tplh = tphl
- WIDE OPERATING VOLTAGE RANGE Vcc (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS7266



DESCRIPTION

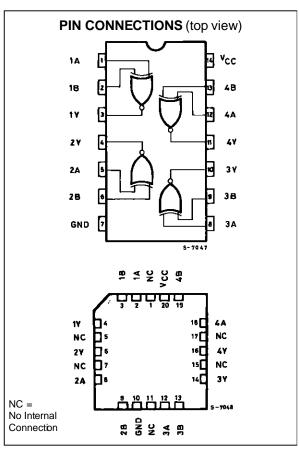
The M54/74HC266/7266 are high speed CMOS QUAD EXCLUSIVE NOR GATES, fabricated in silicon gate C²MOS technology. They have the same high speed performance of LSTTL combined with true CMOS low power consumption.

The HC266 has a high performance N-channel MOS transistor (OPEN DRAIN output).

The HC7266 has an output buffer which is CMOS structure.

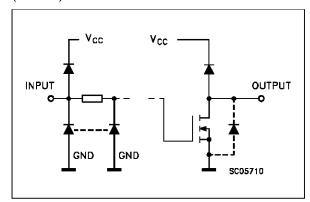
Input and output buffers ensure high noise immunity and stable outputs.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

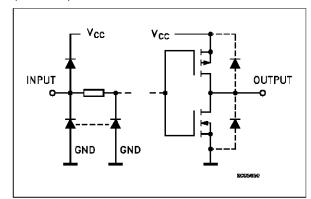


March 1993 1/11

INPUT AND OUTPUT EQUIVALENT CIRCUIT (HC266)



INPUT AND OUTPUT EQUIVALENT CIRCUIT (HC7266)



PIN DESCRIPTION

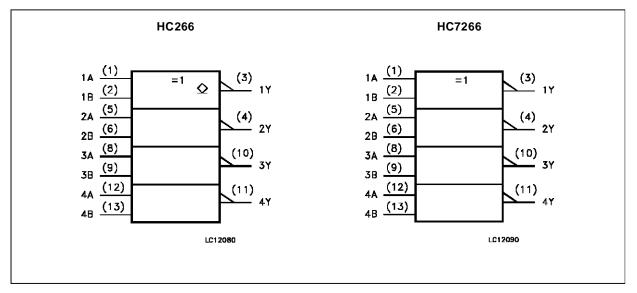
PIN No	SYMBOL	NAME AND FUNCTION
1, 5, 8, 12	1A to 4A	Data Inputs
2, 6, 9, 13	1B to 4B	Data Inputs
3, 4, 10, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	Vcc	Positive Supply Voltage

TRUTH TABLE

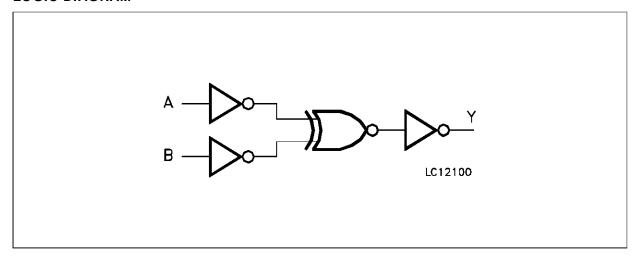
^	В	Υ			
A	В	7266	266		
L	L	Н	Z		
L	Н	L	L		
Н	L	L	L		
Н	Н	Н	Z		

Z: High Impedance

IEC LOGIC SYMBOLS



LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
V_{I}	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{DD} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
lok	DC Output Diode Current	± 20	mA
lo	DC Output Source Sink Current Per Output Pin	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P_{D}	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. (*) 500 mW: ≡ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V_{CC}	Supply Voltage		2 to 6	V
VI	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature: M54HC Series M74HC Series		-55 to +125 -40 to +85	oိ ဂ
t _r , t _f	Input Rise and Fall Time	$V_{CC} = 2 V$	0 to 1000	ns
		$V_{CC} = 4.5 \text{ V}$	0 to 500	
		$V_{CC} = 6 V$	0 to 400	

DC SPECIFICATIONS

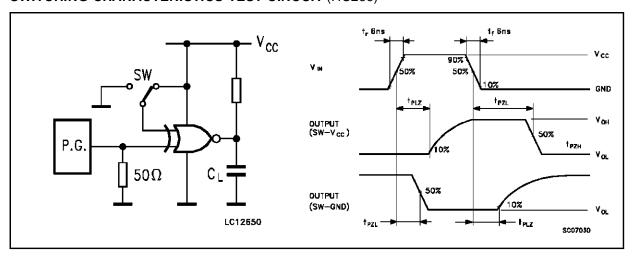
		Test Conditions			Value							
Symbol	Parameter	Vcc			$T_A = 25$ °C 54HC and 74HC		-40 to 85 °C 74HC		-55 to 125 °C 54HC		Unit	
		(V)			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input	2.0			1.5			1.5		1.5		
	Voltage	4.5			3.15			3.15		3.15		V
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input	2.0					0.5		0.5		0.5	
	Voltage	4.5					1.35		1.35		1.35	V
		6.0					1.8		1.8		1.8	
V_{OH}	High Level	2.0	V _I =		1.9	2.0		1.9		1.9		
	Output Voltage	4.5	VI –	I _O =-20 μA	4.4	4.5		4.4		4.4		.,
	(HC7266)	6.0	or		5.9	6.0		5.9		5.9		V
		4.5	V _{IL}	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output	2.0	V _I =			0.0	0.1		0.1		0.1	
	Voltage	4.5	V _I –	I _O = 20 μA		0.0	0.1		0.1		0.1	.,
		6.0	or			0.0	0.1		0.1		0.1	V
		4.5	VIL	I _O = 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I _O = 5.2 mA		0.18	0.26		0.33		0.40	
lı	Input Leakage Current	6.0	V _I = V _{CC} or GND				±0.1		±1		±1	μΑ
l _{OZ}	Output Leakage Current (HC266)	6.0	$V_I = V_{IH} \text{ or } V_{IL}$ $V_O = V_{CC} \text{ or GND}$				±0.5		±5		±10	μΑ
Icc	Quiescent Supply Current	6.0		V _{CC} or GND			1		10		20	μΑ

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6 \text{ ns}$)

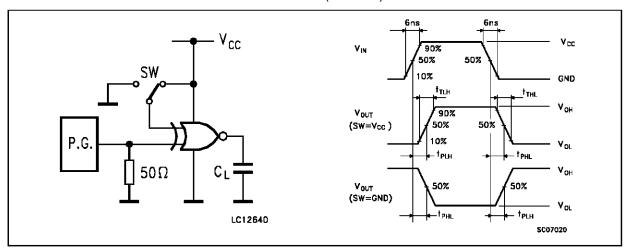
		Test Conditions		Value							
Symbol	Symbol Parameter		Vcc		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		125 °C HC	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{THL}	Output Transition	2.0			30	75		95		110	
	Time (HC266)	4.5			8	15		19		22	ns
		6.0			7	13		16		19	
t _{TLH}	Output Transition	2.0			30	75		95		110	
t _{THL}	Time (HC7266)	4.5			8	15		19		22	ns
		6.0			7	13		16		19	
t _{PLZ}	Propagation	2.0			48	90		115		135	
t _{PZL}	Delay Time	4.5	$R_L = 1K\Omega$		12	18		23		27	ns
	(HC266)	6.0			10	15		20		23	
t _{PLH}	Propagation	2.0			36	90		115		135	
t _{PHL}	Delay Time	4.5			11	18		23		27	ns
	(HC7266)	6.0			9	15		20		23	
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance				20						pF

^(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/4$ (per Gate)

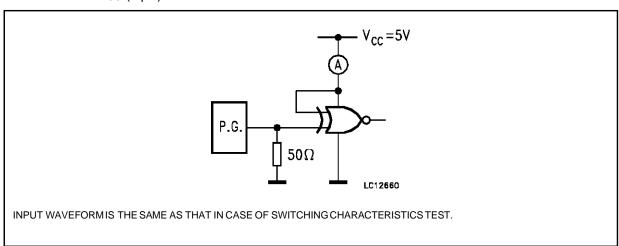
SWITCHING CHARACTERISTICS TEST CIRCUIT (HC266)



SWITCHING CHARACTERISTICS TEST CIRCUIT (HC7266)

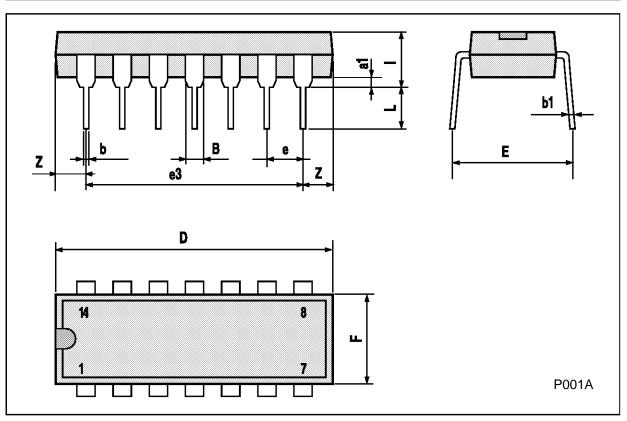


TEST CIRCUIT Icc (Opr.)



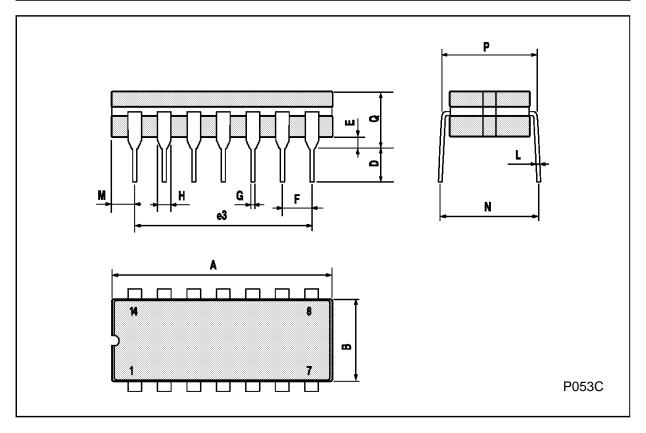
Plastic DIP14 MECHANICAL DATA

DIM.		mm		inch			
Didi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
a1	0.51			0.020			
В	1.39		1.65	0.055		0.065	
b		0.5			0.020		
b1		0.25			0.010		
D			20			0.787	
E		8.5			0.335		
е		2.54			0.100		
e3		15.24			0.600		
F			7.1			0.280	
I			5.1			0.201	
L		3.3			0.130		
Z	1.27		2.54	0.050		0.100	



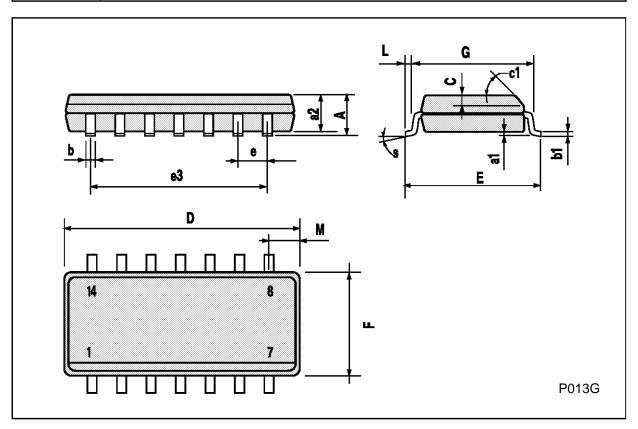
Ceramic DIP14/1 MECHANICAL DATA

DIM.		mm		inch			
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			20			0.787	
В			7.0			0.276	
D		3.3			0.130		
Е	0.38			0.015			
e3		15.24			0.600		
F	2.29		2.79	0.090		0.110	
G	0.4		0.55	0.016		0.022	
н	1.17		1.52	0.046		0.060	
L	0.22		0.31	0.009		0.012	
М	1.52		2.54	0.060		0.100	
N			10.3			0.406	
Р	7.8		8.05	0.307		0.317	
Q			5.08			0.200	



SO14 MECHANICAL DATA

DIM.		mm		inch				
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)				
D	8.55		8.75	0.336		0.344		
Е	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		7.62			0.300			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.68			0.026		
S			8° (r	max.)				



PLCC20 MECHANICAL DATA

DIM.		mm		inch			
Dilli.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	9.78		10.03	0.385		0.395	
В	8.89		9.04	0.350		0.356	
D	4.2		4.57	0.165		0.180	
d1		2.54			0.100		
d2		0.56			0.022		
E	7.37		8.38	0.290		0.330	
е		1.27			0.050		
e3		5.08			0.200		
F		0.38			0.015		
G			0.101			0.004	
М		1.27			0.050		
M1		1.14			0.045		



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